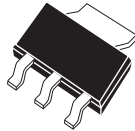


CZT751

SURFACE MOUNT
PNP HIGH CURRENT
SILICON TRANSISTOR



SOT-223 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT751 type is a PNP Silicon Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current applications.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

			UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	2.0	A
Power Dissipation	P_D	2.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

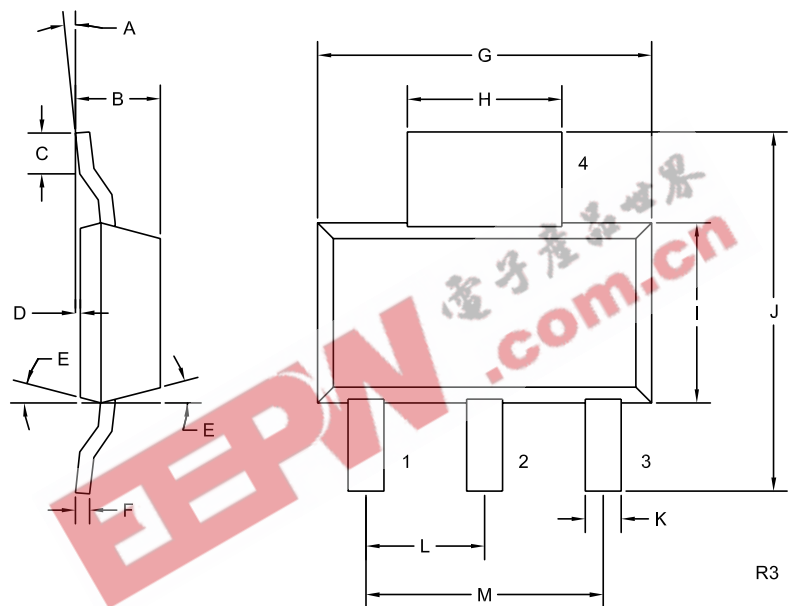
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=80\text{V}$		100	nA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		0.5	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		1.2	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$		1.0	V

R3 (17-June 2004)

ELECTRICAL CHARACTERISTICS: Continued

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=2.0V, I_C=50mA$	75		
h_{FE}	$V_{CE}=2.0V, I_C=500mA$	75		
h_{FE}	$V_{CE}=2.0V, I_C=1.0A$	75		
h_{FE}	$V_{CE}=2.0V, I_C=2.0A$	40		
f_T	$V_{CE}=5.0V, I_C=50mA, f=100MHz$	75		MHz

SOT-223 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

**MARKING CODE:
FULL PART NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	---	0.45	---
D	0.000	0.004	0.00	0.10
E	15°		15°	
F	0.009	0.014	0.23	0.35
G	0.248	0.264	6.30	6.70
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R3)